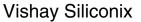
DG2001





Low-Voltage Single SPDT Analog Switch

DESCRIPTION

The DG2001 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed, low on-resistance and small physical size, the DG2001 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2001 is built on Vishay Siliconix's low voltage JI2 process. The DG2001 has a minimum 2000 V, ESD protection, per Method 3015.7. An epitaxial layer prevents latchup. Break-before-make is guaranteed.

The switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FEATURES

- Halogen-free according to IEC 61249-2-21 Definition
- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance R_{ON}: 3 Ω
- Fast Switching t_{ON}: 20 ns, t_{OFF}: 10 ns
- Low Leakage I_{COM}: 0.2 nA
- Low Charge Injection Q_{INJ}: 5 pC
- Low Power Consumption
- TTL/CMOS Compatible
- ESD Protection > 2000 V (Method 3015.7)
- TSOP-6 Package
- Compliant to RoHS Directive 2002/95/EC

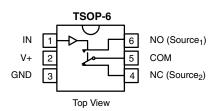
BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- Sample and Hold Circuits

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE							
Logic NC NO							
0	ON	OFF					
1	OFF	ON					

ORDERING INFORMATION						
Temp Range	emp Range Package Part Number					
- 40 °C to 85 °C	TSOP-6	DG2001DV-T1				
- 40 0 10 85 0	1306-0	DG2001DV-T1-E3				

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Pb-free

ROHS COMPLIANT HALOGEN

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ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \degree C$, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Referenced V+ to GND			- 0.3 to + 6	V		
IN, COM, NC, NO ^a	IN, COM, NC, NO ^a			v		
Continuous Current (Any Terminal)			± 50	mA		
Peak Current (Pulsed at 1 ms, 10 % duty cycle)			± 200			
ESD (MIL-STD-883B, Method 3015.7)			> 2000	V		
Storage Temperature (D Suffix)			- 65 to 125	°C		
Power Dissipation (Packages) ^b	TSOP-6 ^c		570	mW		

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC Board.

c. Derate 7 mW/°C above 25 °C.

SPECIFICATIONS (\	/+ = 2 V)						
		Test Conditions Unless Otherwise Specified V+ = 2 V, ± 10 %		Limits - 40 °C to 85 °C			
Parameter	Symbol	$V_{IN} = 0.4 V \text{ or } 1.6 V^{e}$	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Analog Switch	1 -						
Analog Signal Range ^d	V _{NO} , V _{NC} V _{COM}		Full	0		V+	V
On-Resistance	R _{ON}	V+ = 1.8 V, V _{COM} = 1 V, I _{NO} , I _{NC} = 10 mA	Room Full		15 17	30 32	0
R _{ON} Flatness ^d	R _{ON} Flatness	V+ = 1.8 V, V_{COM} = 0 V to V+, I_{NO} , I_{NC} = 10 mA	$1.8 \text{ V}, \text{ V}_{\text{COM}} = 0 \text{ V to V+}, \text{ I}_{\text{NO}}, \text{ I}_{\text{NC}} = 10 \text{ mA}$ Room		5		Ω
Switch Off	I _{NO(off)} I _{NC(off)}	V+ = 2.2 V	Room Full	- 300 - 3.5		300 3.5	pA nA
Leakage Current ^g	I _{COM(off)}	V _{NO} , V _{NC} = 0.5 V/1.5 V, V _{COM} = 1.5 V/0.5 V	Room Full	- 300 - 3.5		300 3.5	pA nA
Channel-On Leakage Current ^g	I _{COM(on)}	V+ = 2.2 V, V _{NO} , V _{NC} = V _{COM} = 0.5 V/1.5 V	Room Full	- 350 - 3.5		300 3.5	pA nA
Digital Control			•		1		
Input High Voltage	V _{INH}		Full	1.6			V
Input Low Voltage	V _{INL}		Full			0.4	V
Input Capacitance	C _{in}		Full		4		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	1		1	μA
Dynamic Characteristics	•		•				
Turn-On Time	t _{ON}		Room Full		30	50 53	
Turn-Off Time	t _{OFF}	$V_{NO}~\text{or}~V_{NC}$ = 1.5 V, R_L = 300 $\Omega,~C_L$ = 35 pF	Room Full		15	30 33	ns
Break-Before-Make Time	t _d		Room	1	15		
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room		1	10	рС
Off-Isolation ^d	OIRR		Room		- 71		-10
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 70		dB
N_O , N_C Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room		17		pF
Channel-On Capacitance ^d	C _{ON}		Room		50		
Power Supply							
Power Supply Range	V+			1.8		2.20	V
Power Supply Current	l+	V _{IN} = 0 V or V+			0.01	1	μA
Power Consumption	P _C					2.2	μW

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SPECIFICATIONS (\	/+ = 3 V)						
		Test Conditions Unless Otherwise Specified V+ = 3 V, ± 10 %		Limits - 40 °C to 85 °C			
Parameter	Symbol	$V_{IN} = 0.4 \text{ V or } 2 \text{ V}^{e}$	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Analog Switch	•		•		•		
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	v
On-Resistance	R _{ON}	V+ = 2.7 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 10 mA	Room Full		5 6	9.2 10.2	
R _{ON} Flatness ^d	R _{ON} Flatness	V+ = 2.7 V, V _{COM} = 0 V to V+, I _{NO} , I _{NC} = 10 mA	Room		3		Ω
Switch Off	I _{NO(off)} , I _{NC(off)}	V+ = 3.3 V	Room Full	- 400 - 4.5		400 4.5	pA nA
Leakage Current ^g	I _{COM(off)}	V_{NO} , V_{NC} = 1 V/3 V, V_{COM} = 3 V/1 V	Room Full	- 400 - 4.5		400 4.5	pA nA
Channel-On Leakage Current ^g	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 1 V/3 V	Room Full	- 450 - 4.5		400 4.5	pA nA
Digital Control			1		•	1	
Input High Voltage	V _{INH}			2			v
Input Low Voltage	V _{INL}		Full			0.4	v
Input Capacitance	C _{in}		Full		4		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	1		1	μA
Dynamic Characteristics					I	1	
Turn-On Time	t _{ON}		Room Full		24	45 48	
Turn-Off Time	t _{OFF}	V_{NO} or V_{NC} = 2 V, R_L = 300 Ω , C_L = 35 pF	Room Full		12	30 33	ns
Break-Before-Make Time	t _d		Room	1	13		
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room		3	10	рС
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega_2, C_1 = 5 pF, f = 1 MHz$	Room		- 71		٩D
Crosstalk ^d	X _{TALK}	$n_{L} = 50.52, O_{L} = 5 \text{ pr}, 1 = 1 \text{ MHZ}$	Room		- 70		dB
N _O , N _C Off Capacitance ^d	C _{NO(off)} , C _{NC(off)}	V _{IN} = 0 V or V+, f = 1 MHz			17		pF
Channel-On Capacitance ^d	C _{ON}		Room		50		
Power Supply				l		1	L
Power Supply Range	V+			2.7		3.3	V
Power Supply Current	l+				0.01	1	μA
Power Consumption	P _C	V _{IN} = 0 V or V+				3.3	μW

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SPECIFICATIONS (\	/+ = 5 V)						
		Test Conditions Unless Otherwise Specified V+ = 5 V, ± 10 %		Limits - 40 °C to 85 °C			
Parameter	Symbol	$V_{IN} = 0.8 \text{ V or } 2.4 \text{ V}^{e}$	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Analog Switch	<u> </u>		<u> </u>	<u> </u>		<u> </u>	1
Analog Signal Range ^d	V _{NO} , V _{NC} V _{COM}		Full	0		V+	v
On-Resistance	R _{ON}	V+ = 4.5 V, V _{COM} = 3 V, I _{NO} , I _{NC} = 10 mA	Room Full		3 4	7 8	
R _{ON} Flatness ^d	R _{ON} Flatness	V+ = 4.5 V, V_{COM} = 0 V to V+, I_{NO} , I_{NC} = 10 mA	Room		2		Ω
Switch Off	I _{NO(off)} I _{NC(off)}	V+ = 5.5 V	Room Full	- 900 - 5.5		900 5.5	pA nA
Leakage Current ^g	I _{COM(off)}	V_{NO} , V_{NC} = 1 V/4.5 V, V_{COM} = 4.5 V/1 V	Room Full	- 900 - 5.5		900 5.5	pA nA
Channel-On Leakage Current ^g	I _{COM(on)}	V+ = 5.5 V, V+ = 5.5 V V _{NO} , V _{NC} = V _{COM} = 1 V/4.5 V	Room Full	- 1000 - 5.5		1000 5.5	pA nA
Digital Control			•				
Input High Voltage	V _{INH}		Full	2.4			v
Input Low Voltage	V _{INL}		Full			0.8	v
Input Capacitance	C _{in}		Full		4		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	1		1	μA
Dynamic Characteristics	•		•				
Turn-On Time	t _{ON}		Room Full		20	37 40	
Turn-Off Time	t _{OFF}	$V_{NO} \text{ or } V_{NC}$ = 3 V, R_L = 300 Ω, C_L = 35 pF	Room Full		10	27 30	ns
Break-Before-Make Time	t _d		Room	1	10		
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_GEN = 0 V, R_GEN = 0 Ω	Room		7	10	рС
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room		- 71		-10
Crosstalk ^d	X _{TALK}	$n_{L} = 50.52, O_{L} = 5.00, T = 1.0012$	Room		- 70		dB
Source-Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room		17		pF
Channel-On Capacitance ^d	C _{ON}		Room		50		
Power Supply	•						
Power Supply Range	V+			4.5		5.5	V
Power Supply Current	l+	V _{IN} = 0 V or V+			0.01	1	μΑ
Power Consumption	P _C					5.5	μW

Notes:

a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

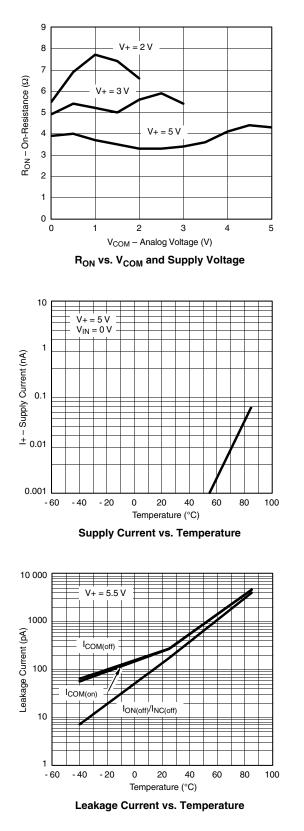
f. Guaranteed by 5 V leakage testing, not production tested.

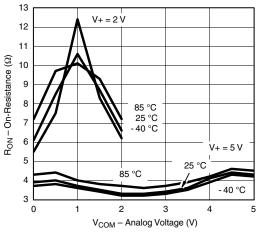
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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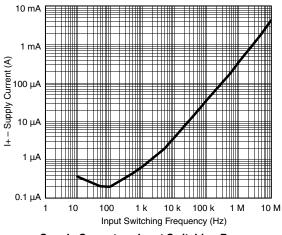


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

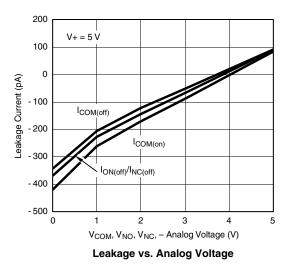




R_{ON} vs. Analog Voltage and Temperature



Supply Current vs. Input Switching Frequency



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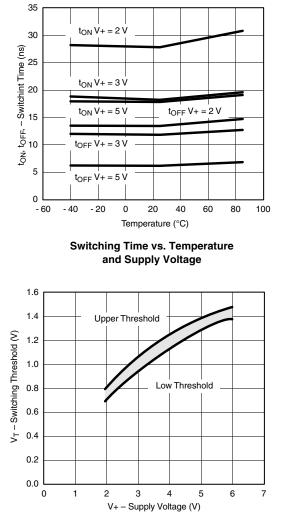
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DG2001

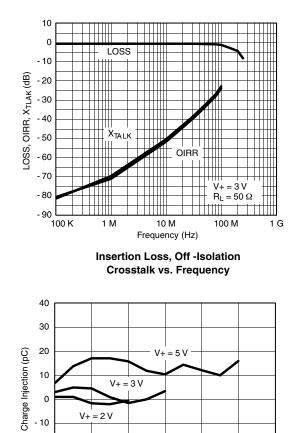
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Switching Threshold vs. Supply Voltage



0

- 10

- 30

- 40

0

ά - 20 V+ = 2 V

1

2

3

V_{COM} – Analog Voltage (V)

Charge Injection vs. Analog Voltage

4

5

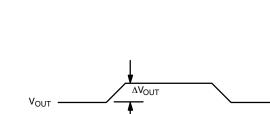
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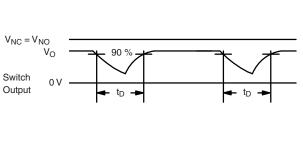


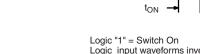
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Л

ΔV_{OUT} V_{OUT}



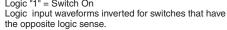




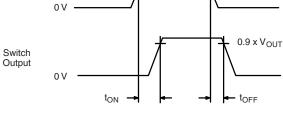
+ 3 V

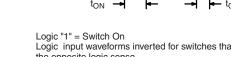
Logic

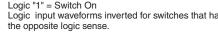
Input

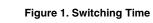


50 %







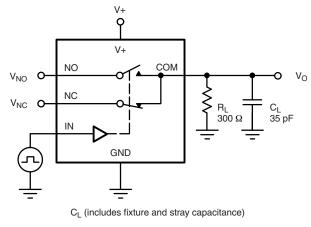


Logic

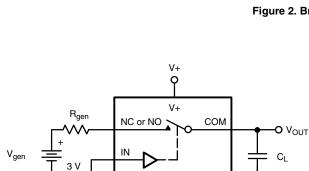
Input

3 V

0 V

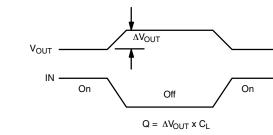






GND

-

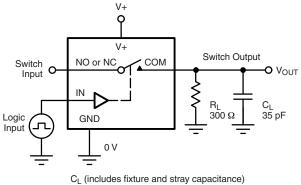


IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection



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RL $V_{OUT} = V_{COM}$ R₁ R_{ON}

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t_r < 20 ns

t_f < 20 ns

t_r < 5 ns

ṫ_f < 5 ns

DG2001

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TEST CIRCUITS

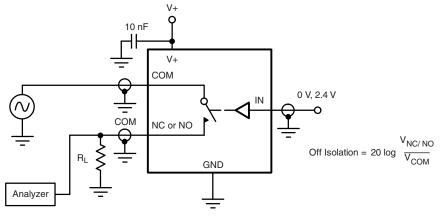


Figure 4. Off-Isolation

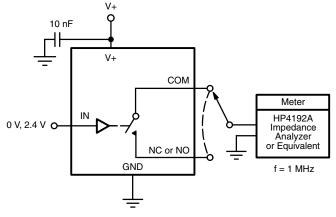


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71398.

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Package Information

Vishay Siliconix

TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



	MIL	LIMETER	RS	INCHES				
Dim	Min	Nom	Max	Min Nom		Max		
Α	0.91	-	1.10	0.036	-	0.043		
A ₁	0.01	-	0.10	0.0004	-	0.004		
A ₂	0.90	-	1.00	0.035	0.038	0.039		
b	0.30	0.32	0.45	0.012	0.013	0.018		
С	0.10	0.15	0.20	0.004	0.006	0.008		
D	2.95	3.05	3.10	0.116	0.116 0.120			
Е	2.70	2.85	2.98	0.106	0.112	0.117		
E ₁	1.55	1.65	1.70	0.061	0.065	0.067		
е		0.95 BSC			0.0374 BSC	;		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079		
L	0.32	-	0.50	0.012	-	0.020		
L ₁		0.60 Ref			0.024 Ref			
L ₂		0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-		
θ	0°	4°	8°	0°	4°	8°		
θ_1	7° Nom			7° Nom				
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540								



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